MA795WK

Silicon epitaxial planer type

For the switching circuit

■ Features

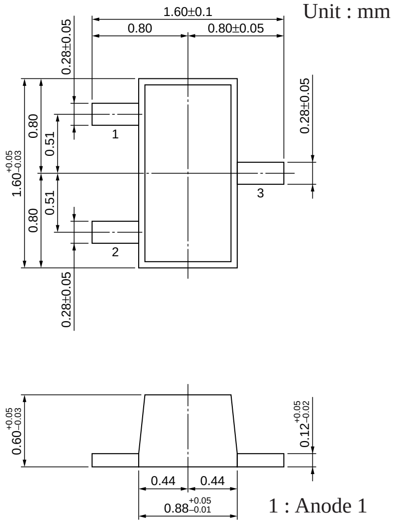
- Extra-small (SS-Mini type) package, enabling high-density mounting
- Low V_F type (I_F=1mA), optimum for low voltage rectification of V_F= 0.3V or less
- Fast reverse recovery time t_{rr}, optimum for high-frequency rectification

■ Absolute Maximum Ratings (Ta= 25˚C)

Parameter		Symbol	Rating	Unit
Reverse voltage (DC)		V_R	30	V
Peak reverse voltage		V_{RM}	30	V
Peak forward current	Single	I_{FM}	150	mA
	Double		110*	
Forward current	Single	I_F	30	mA
	Double		20*	
Junction temperature		T_j	125	˚C
Storage temperature		T_{stg}	– 55 to +125	˚C

* Use value per chip

Unit : mm

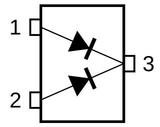


1 : Anode 1
2 : Anode 2
3 : Cathode 1
Cathode 2

SS-Mini Type Package (3-pin)

Marking Symbol : M3D

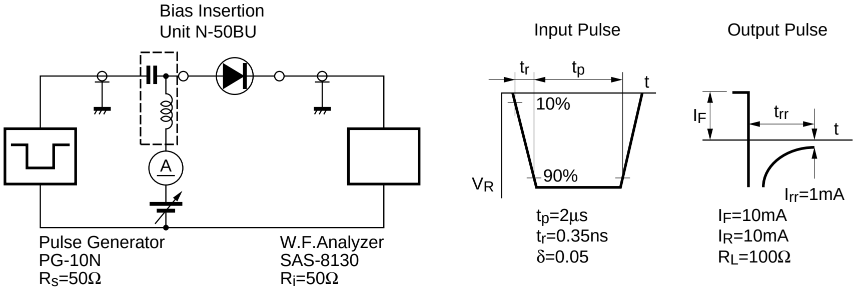
■ Internal Connection



■ Electrical Characteristics (Ta= 25˚C)

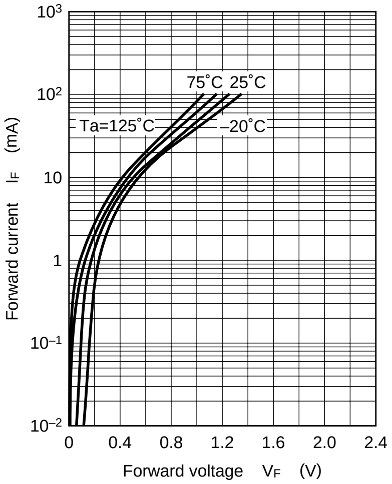
Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	V_R= 30V			50	µA
Forward voltage (DC)	V_{F1}	I_F=1mA			0.3	V
	V_{F2}	I_F= 30mA			1	V
Terminal capacitance	C_t	V_R =1V, f=1MHz		1.5		pF
Reverse recovery time	t_{rr}*	I_F = I_R=10mA I_{rr}= 1mA , R_L=100Ω		1		ns
Detection efficiency	η	V_{in}= 3V(peak), f= 30MHz R_L= 3.9kΩ, C_L=10pF		65		%

Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.
2. Rated input/output frequency : 2000MHz
3. * t_{rr} measuring circuit

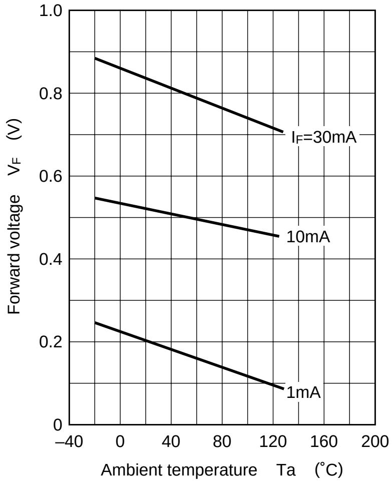


■ Marking

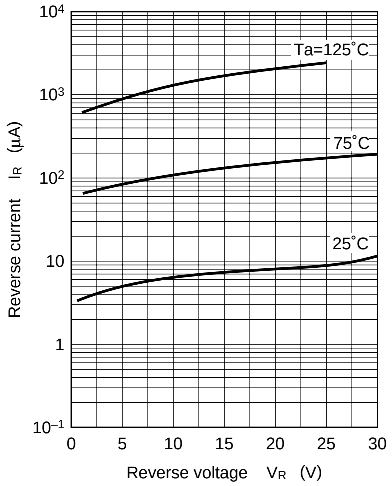
$I_F - V_F$



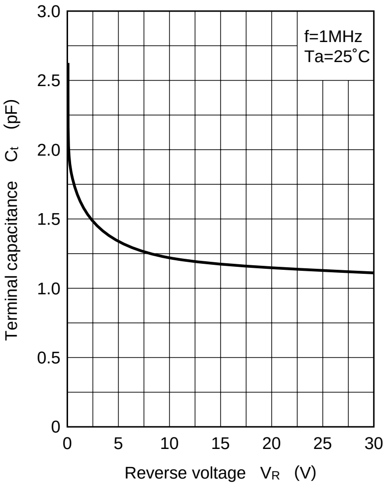
$V_F - Ta$



$I_R - V_R$



$C_t - V_R$



$I_R - Ta$